

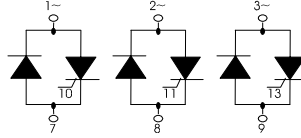
## Three Phase AC Controller Modules

### PSUH 36

$I_{RMS}$  = 3 x 39A  
 $V_{RRM}$  = 400-1600 V

$V_{RSM}$ $V_{DSM}$	$V_{RRM}$ $V_{DRM}$	Type
500	400	PSUH 36/04
900	800	PSUH 36/08
1300	1200	PSUH 36/12
1500	1400	PSUH 36/14
*1700	*1600	PSUH 36/16

\* Delivery on request



Symbol	Test Conditions	Maximum Ratings
$I_{RMS}$	$T_C = 85^\circ C$ , 50-400 Hz (per phase)	39 A
$I_{TRMS}$	$T_{VJ} = T_{VJM}$	28 A
$I_{TAVM}$	$T_C = 85^\circ C$ 180° sine	18 A
$I_{TSM}$	$T_{VJ} = 45^\circ C$ t = 10 ms (50 Hz), sine	320 A
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	350 A
	$T_{VJ} = T_{VJM}$ t = 10 ms (50 Hz), sine	280 A
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	310 A
$\int i^2 dt$	$T_{VJ} = 45^\circ C$ t = 10 ms (50 Hz), sine	500 A <sup>2</sup> s
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	520 A <sup>2</sup> s
	$T_{VJ} = T_{VJM}$ t = 10 ms (50 Hz), sine	390 A <sup>2</sup> s
	$V_R = 0$ t = 8.3 ms (60 Hz), sine	400 A <sup>2</sup> s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 20$ A	150 A/ $\mu$ s
	f = 50Hz, $t_p = 200\mu$ s	
	$V_D = 2/3 V_{DRM}$	
	$I_G = 0.3$ A non repetitive, $I_T = I_{TAVM}$	500 A/ $\mu$ s
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $V_{DR} = 2/3 V_{DRM}$	1000 V/ $\mu$ s
	$R_{GK} = \infty$ , method 1 (linear voltage rise)	
$P_{GM}$	$T_{VJ} = T_{VJM}$ $t_p = 30\mu$ s	10 W
	$I_T = I_{TAVM}$ $t_p = 300\mu$ s	5 W
$P_{GAVM}$		0.5 W
$V_{RGM}$		10 V
$T_{VJ}$		-40 ... + 125 °C
$T_{VJM}$		125 °C
$T_{stg}$		-40 ... + 125 °C
$V_{ISOL}$	50/60 HZ, RMS t = 1 min	2500 V ~
	$I_{ISOL} \leq 1$ mA t = 1 s	3000 V ~
$M_d$	Mounting torque (M5)	2-2.5 Nm
Weight	typ.	100 g

### Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Package with metal base plate
- UL registered E 148688

### Applications

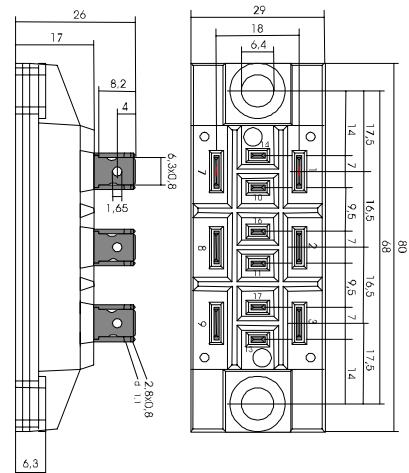
- Switching and control of three phase AC circuits
- Light and temperature control
- Softstart AC motor controller
- Solid state switches

### Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

### Package, stil and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions	Characteristic Value	
$I_D, I_R$	$T_{VJ} = T_{VJM}, V_R = V_{RRM}, V_D = V_{DRM}$	$\leq 5$ mA	
$V_T$	$I_T = 45A, T_{VJ} = 25^\circ C$	$\leq 1.45$ V	
$V_{TO}$	For power-loss calculations only ( $T_{VJ} = T_{VJM}$ )	0.85 V	
$r_T$		13 m $\Omega$	
$V_{GT}$	$V_D = 6V$	$T_{VJ} = 25^\circ C$	$\leq 1.0$ V
		$T_{VJ} = -40^\circ C$	$\leq 1.2$ V
$I_{GT}$	$V_D = 6V$	$T_{VJ} = 25^\circ C$	$\leq 65$ mA
		$T_{VJ} = -40^\circ C$	$\leq 80$ mA
$V_{GD}$	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	$\leq 0.2$ V	
$I_{GD}$	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	$\leq 5$ mA	
$I_L$	$T_{VJ} = 25^\circ C, t_p = 10\mu s$	$\leq 150$ mA	
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$		
$I_H$	$T_{VJ} = 25^\circ C, V_D = 6V, R_{GK} = \infty$	$\leq 100$ mA	
$t_{gd}$	$T_{VJ} = 25^\circ C, V_D = 1/2 V_{DRM}$	$\leq 2$ $\mu s$	
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$		
$t_q$	$T_{VJ} = T_{VJM}, I_T = 20A, t_p = 200\mu s, V_R = 100V$	150 $\mu s$	
	$-di/dt = 10A/\mu s, dv/dt = 15V/\mu s, V_D = 2/3 V_{DRM}$		
$R_{thJC}$	per thyristor; sine 180°el	1.3 K/W	
	per module	0.22 K/W	
$R_{thJK}$	per thyristor; sine 180° el	1.5 K/W	
	per module	0.25 K/W	
$d_s$	Creeping distance on surface	16.1 mm	
$d_A$	Creeping distance in air	6.0 mm	
$a$	Max. allowable acceleration	50 m/s <sup>2</sup>	